

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
20V	18mΩ@4.5V	5A
	22mΩ@2.5V	

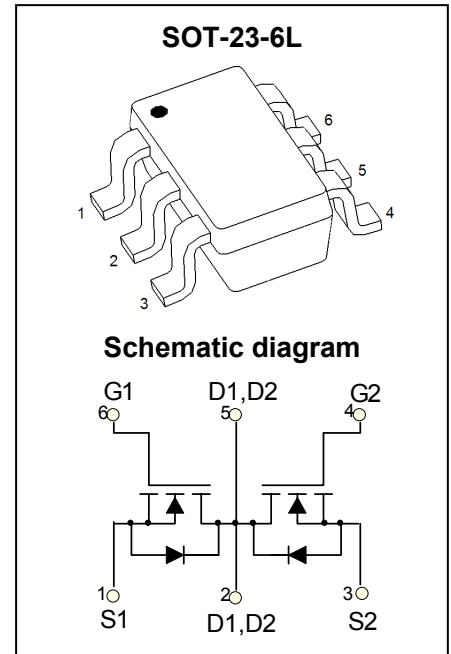
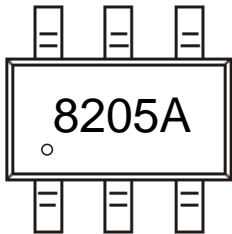
### Feature

- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance

### Application

- Power Switching Application

### MARKING:



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	20	V
Gate - Source Voltage	$V_{GS}$	$\pm 10$	V
Continuous Drain Current <sup>1,5</sup>	$I_D$	5	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	20	A
Power Dissipation <sup>4,5</sup>	$P_D$	0.65	W
Thermal Resistance from Junction to Ambient <sup>5</sup>	$R_{\theta JA}$	190	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

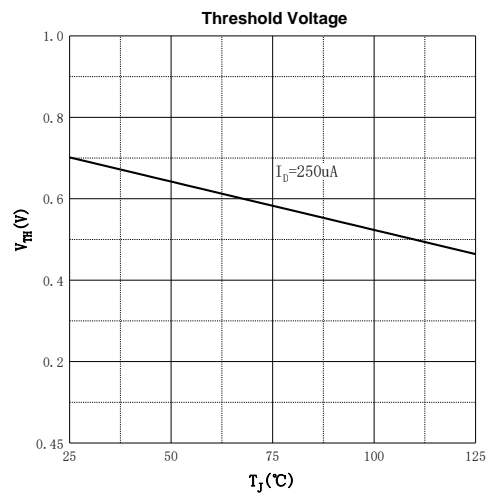
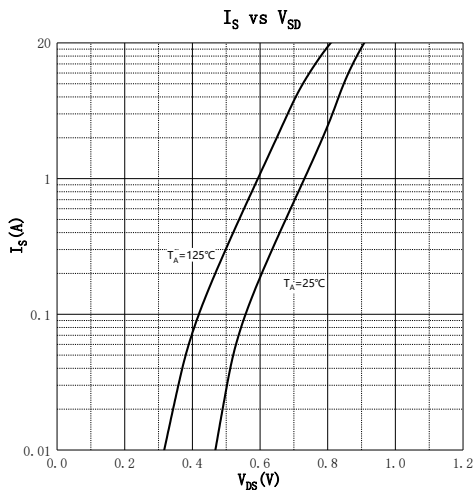
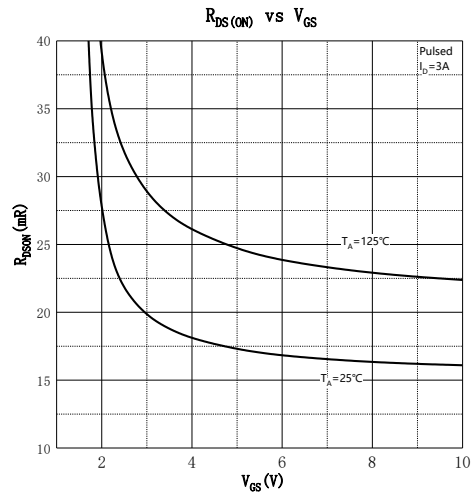
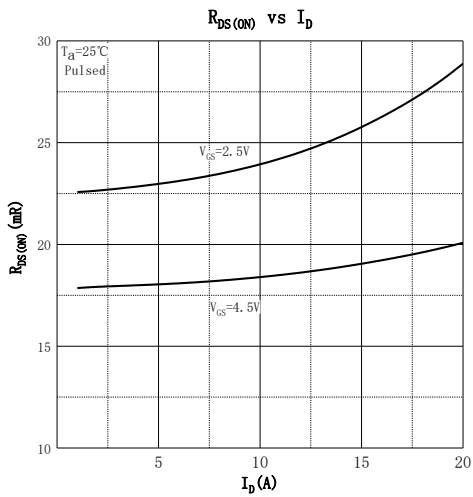
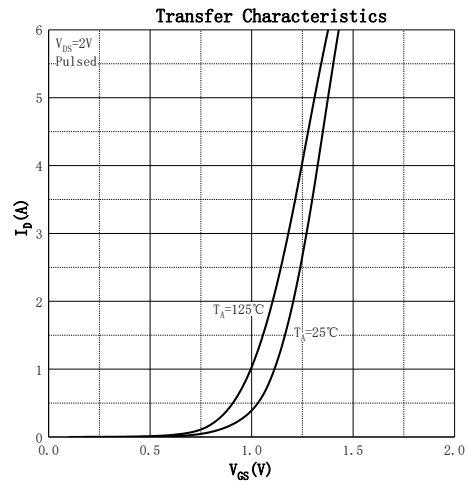
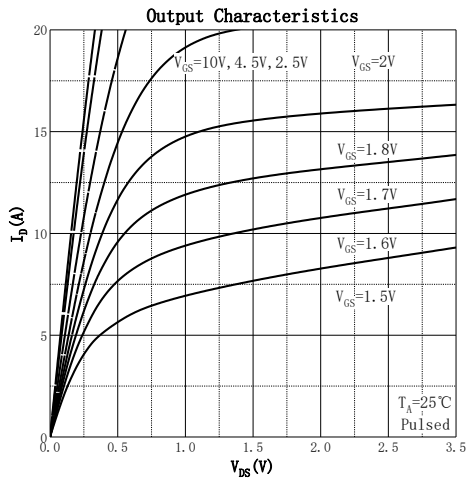
**MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 18V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>3</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.4	0.7	1	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 3A$	15	18	26	m $\Omega$
		$V_{GS} = 2.5V, I_D = 3A$	18	22	35	
Forward Transconductance	$g_{FS}$	$V_{DS} = 5V, I_D = 4.5A$		10.5		S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		354		pF
Output Capacitance	$C_{oss}$			66		
Reverse Transfer Capacitance	$C_{rss}$			57		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.5		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 10V, V_{GS} = 4.5V, I_D = 5A$		10		nC
Gate-source Charge	$Q_{gs}$			2.8		
Gate-drain Charge	$Q_{gd}$			3.0		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_L = 2\Omega, R_G = 3\Omega$		15		ns
Turn-on Rise Time	$t_r$			7		
Turn-off Delay Time	$t_{d(off)}$			35		
Turn-off Fall Time	$t_f$			18		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 1.25A$			1.2	V

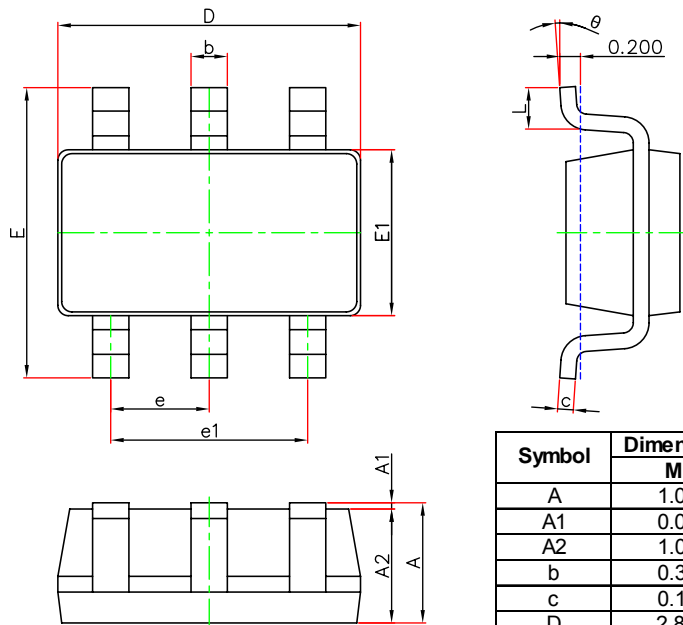
**Notes :**

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 4.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .
- 5.Device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

**Typical Characteristics**



## SOT-23-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)